

DIODE ARRAY PRODUCT SPECIFICATION

MONOLITHIC AIR ISOLATED DIODE ARRAY

FEATURES:

- HERMETIC CERAMIC PACKAGE
- $B_v > 75V$ at $5\mu A$
- $I_r < 100nA$ at $40V$
- $C < 4.0 pF$

Absolute Maximum Ratings:

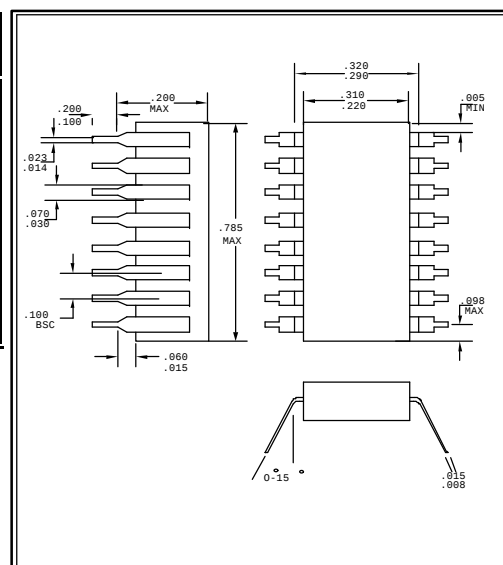
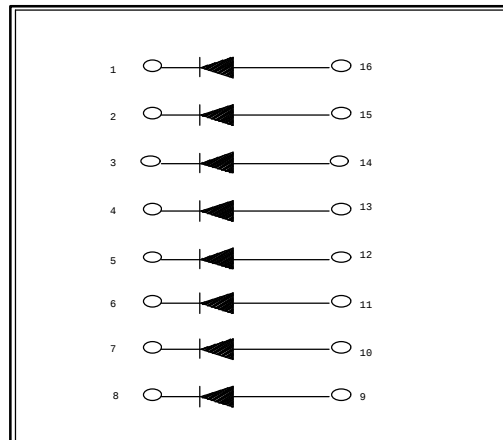
Symbol	Parameter	Limit	Unit
VBR(R) *1 *2	Reverse Breakdown Voltage	75	Vdc
IO *1 *3	Continuous Forward Current	300	mAdc
IFSM *1	Peak Surge Current (tp= 1/120 s)	500	mAdc
PT1 *4	Power Dissipation per Junction @ 25°C	400	mW
PT2 *4	Power Dissipation per Package @ 25°C	600	mW
Top	Operating Junction Temperature Range	-65 to +150	°C
Tstg	Storage Temperature Range	-65 to +200	°C

NOTE 1: Each Diode

NOTE 2: Pulsed: PW = 100ms max.; duty cycle $\leq$ 20%

NOTE 3: Derate at 2.4mA/°C above +25 °C

NOTE 4: Derate at 4.0mW/°C above +25 °C



Electrical Characteristics (Per Diode) @ 25°C unless otherwise specified

PACKAGE OUTLINE

Symbol	Parameter	Conditions	Min	Max	Unit
Vf1	Forward Voltage	If = 100mA _{dc} *1		1	V _{dc}
IR1	Reverse Current	V _R = 40 V _{dc}		0.1	μA _{dc}
IR2	Reverse Current	V _R = 20 V _{dc}		25	nA _{dc}
C _t	Capacitance (pin to pin)	V _R = 0V _{dc} ; f = 1 MHz		4.0	pF
t _{fr}	Forward Recovery Time	If = 100mA _{dc}		15	ns
t _{rr}	Reverse Recovery Time	If = IR = 10mA _{dc} , i _{rr} = 1 mA _{dc} , R _L = 100 ohms		10	ns
VF5	Forward Voltage Match	If = 10 mA		5	mV

NOTE 1: Pulsed: PW = 300us +/- 50us, duty cycle ≤ 2%, 90us after leading edge

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